

Recitation 16: Small Signal Model of p-n Diode

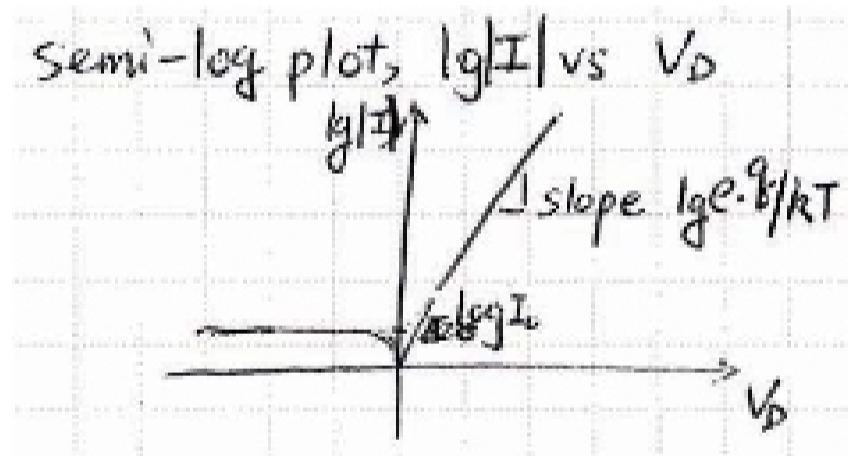
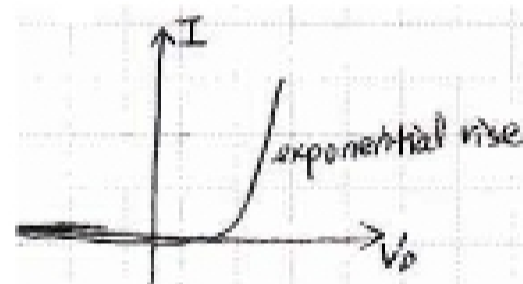
Review

Last week we learned about the IV characteristic of p-n diode:

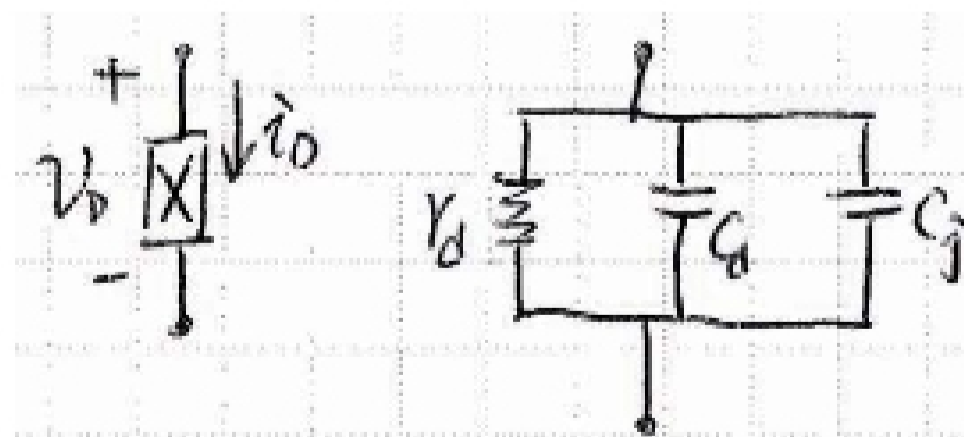
$$I = I_o(e^{qV_o/kT} - 1)$$

where $I_o = qAn_i^2 \left(\frac{1}{N_a} \frac{D_n}{w_p - x_p} + \frac{1}{N_d} \frac{D_p}{w_n - x_n} \right)$

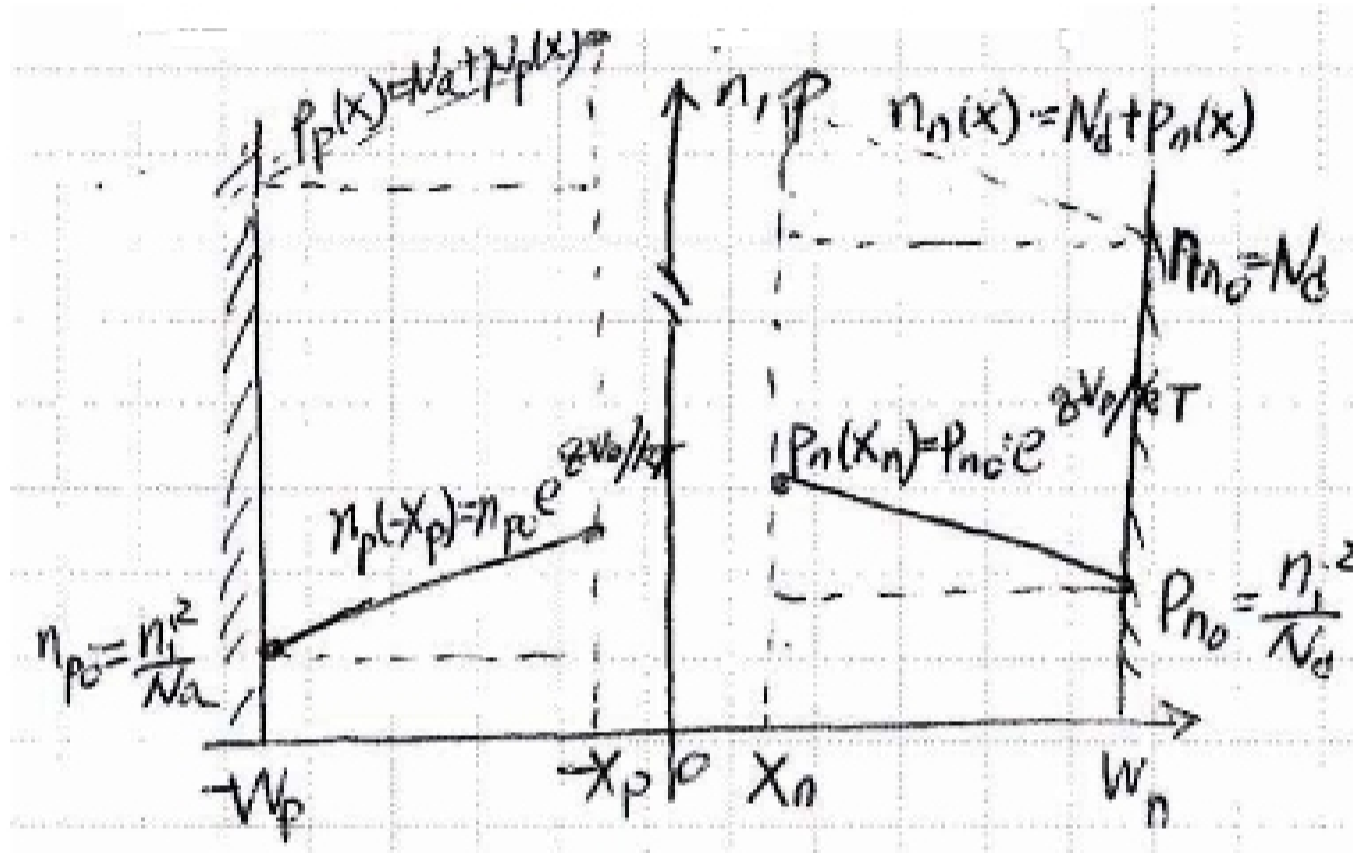
If we plot,



Yesterday, we discussed the small signal model for p-n diode. Under forward bias, the small signal (ss) model of a p-n diode is:

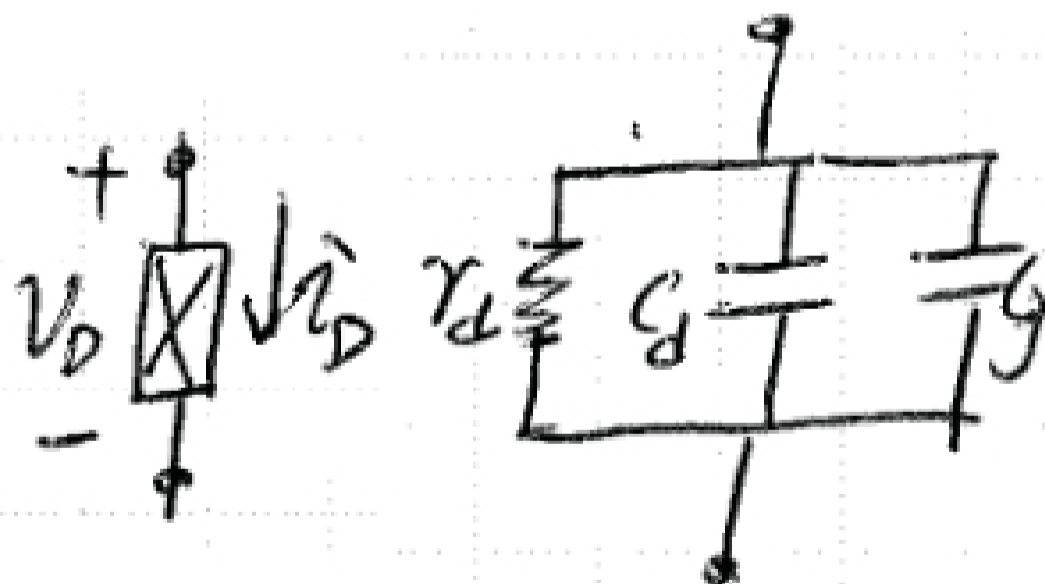


C_j is the junction capacitance as we talked about before, C_d is called "diffusion capacitance", this is new



Small signal circuit model of p-n diode: (two terminal device)

In a small signal model, we have linearized conductance (resistance) and capacitances.



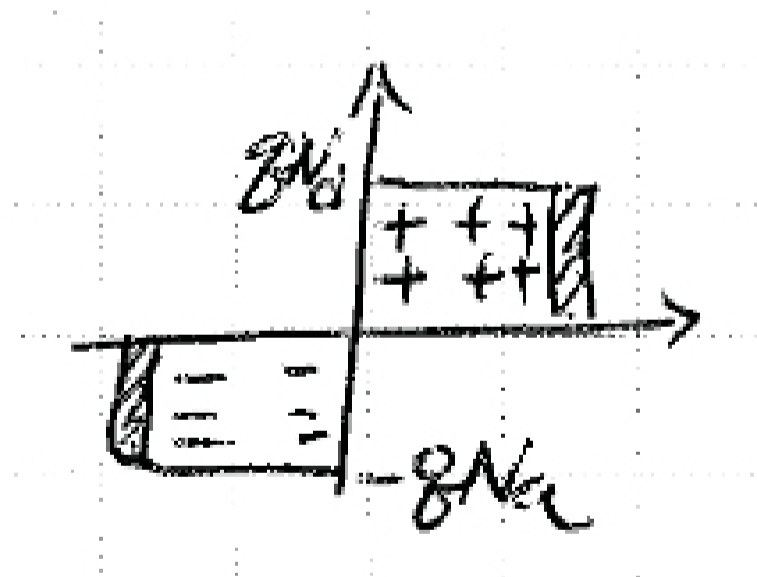
Linearized Conductance (Resistance)

$$\begin{aligned}
 \gamma_d &= \frac{1}{g_d}, \quad g_d = \left. \frac{\delta i_D}{\delta V_D} \right|_{V_D} = \left. \frac{\delta I_o \cdot (e^{qV_D/kT} - 1)}{\delta V_D} \right|_{V_D} \\
 &= I_o \cdot \frac{q}{kT} e^{qV_D/kT} \\
 &= \frac{q}{kT} \cdot (I_D + I_o) \\
 &= \frac{q}{kT} I_D, \quad \frac{kT}{q} = V_{th} \\
 \Rightarrow \gamma_d &= \frac{V_{th}}{I_D}
 \end{aligned}$$

V_{th} constant, the larger operating current I_D , the smaller is γ_d

Depletion Capacitance (due to p-n junction)

$$\begin{aligned}
 C_{j0} &= \frac{\epsilon_s}{x_{do}} = \sqrt{\frac{q\epsilon_s N_a N_d}{2(N_a + N_d)\phi_B}} \\
 C_j(V_D) &= \frac{C_{j0}}{\underbrace{\sqrt{1 - \frac{V_D}{\phi_B}}}_{\text{capacitance/unit area!}}} \quad \text{For forward bias limit } V_D \text{ to } \frac{\phi_B}{2}
 \end{aligned}$$



Diffusion Capacitance

For this, we need to look at the majority carrier concentration as well. To keep quasi-neutral,

$$\begin{aligned}
 n_n(x) &= N_d + p_n(x) \\
 p_p(x) &= N_a + n_p(x)
 \end{aligned}$$